

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Withdrawn) An apparatus comprising:

a loading chamber;

a first chamber for forming a light-emitting film by a liquid jet method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

2. (Withdrawn) An apparatus comprising:

a loading chamber;

a common chamber;

a first chamber for forming a light-emitting film by a liquid jet method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading

chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

3. (Withdrawn) An apparatus comprising:

a loading chamber;

a first chamber for forming a light-emitting film by a printing method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

4. (Withdrawn) An apparatus comprising:

a loading chamber;

a common chamber;

a first chamber for forming a light-emitting film by a printing method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

5. (Withdrawn) An apparatus comprising:

a loading chamber;

a first chamber for forming a light-emitting film by a spray method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the first chamber to the third chamber and the unloading chamber.

6. (Withdrawn) An apparatus comprising:

a loading chamber;

a common chamber;

a first chamber for forming a light-emitting film by a spray method;

a second chamber for forming a conductive film by a sputtering method;

a third chamber for forming an insulating film by a sputtering method; and

an unloading chamber,

wherein a substrate is so supported that an angle subtended by a surface of the substrate to be treated and the direction of gravity is within from 0 to 30° in all of the loading chamber, the common chamber, the first chamber to the third chamber and the unloading chamber.

7. (Withdrawn) An apparatus according to any one of claims 1 to 6, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

8. (Withdrawn) An apparatus according to any one of claims 1 to 6, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

9. (Withdrawn) An apparatus according to any one of claims 1 to 6, wherein the conductive film is an oxide conductive film.

10. (Withdrawn) An apparatus according to any one of claims 1 to 6, wherein the insulating film comprises silicon nitride.

11. (Withdrawn) An apparatus according to any one of claims 1 to 6, wherein the loading chamber and the unloading chamber are constituted as a unitary structure.

12. (Original) A method of producing a light-emitting device comprising the steps of:  
forming a light-emitting film on an electrode by an ink jet method;  
forming a conductive film on the light-emitting film by a sputtering method; and  
forming an insulating film on the conductive film by a sputtering method,  
wherein the light-emitting film forming step, the conductive film forming step and the

insulating film forming step are carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

13. (Original) A method of producing a light-emitting device comprising the steps of:

forming a light-emitting film on an electrode by a printing method;

forming a film on the light-emitting film by a sputtering method; and

forming an insulating film on the conductive film by a sputtering method,

wherein the light-emitting film forming step, the conductive film forming step and the insulating film forming step are carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

14. (Original) A method of producing a light-emitting device comprising the steps of:

forming a light-emitting film on an electrode by a spray method;

forming a conductive film on the light-emitting material by a sputtering method; and

forming an insulating film on the conductive film by a sputtering method,

wherein the light-emitting film forming step, the conductive film forming step and the insulating film forming step are carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

15. (Currently amended) A method of producing a light-emitting device according to ~~any one of claims 12 to 14~~ claim 12, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

16. (Currently amended) A method of producing a light-emitting device according to ~~any one of claims 12 to 14~~ claim 12, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

17. (Currently amended) A method of producing a light-emitting device according to ~~any one of claims 12 to 14~~ claim 12, wherein the conductive film is an oxide conductor film.

18. (Currently amended) A method of producing a light-emitting device according to ~~any one of claims 12 to 14~~ claim 12, wherein the insulating film comprises silicon nitride.

19. (New) A method of producing a light-emitting device according to claim 13, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

20. (New) A method of producing a light-emitting device according to claim 13, wherein the

conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

21. (New) A method of producing a light-emitting device according to claim 13, wherein the conductive film is an oxide conductor film.

22. (New) A method of producing a light-emitting device according to claim 13, wherein the insulating film comprises silicon nitride.

23. (New) A method of producing a light-emitting device according to claim 14, wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

24. (New) A method of producing a light-emitting device according to claim 14, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

25. (New) A method of producing a light-emitting device according to claim 14, wherein the conductive film is an oxide conductor film.

26. (New) A method of producing a light-emitting device according to claim 14, wherein the

insulating film comprises silicon nitride.

27. (New) A method of producing a light-emitting device comprising the steps of:

forming a light-emitting film on an electrode by an ink jet method;

forming a conductive film on the light-emitting film; and

forming an insulating film on the conductive film,

wherein at least one of the light-emitting film forming step, the conductive film forming step and the insulating film forming step is carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

28. (New) A method of producing a light-emitting device comprising the steps of:

forming a light-emitting film on an electrode by a printing method;

forming a film on the light-emitting film; and

forming an insulating film on the conductive film,

wherein at least one of the light-emitting film forming step, the conductive film forming step and the insulating film forming step is carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

29. (New) A method of producing a light-emitting device comprising the steps of:

forming a light-emitting film on an electrode by a spray method;

forming a conductive film on the light-emitting material; and  
forming an insulating film on the conductive film,  
wherein at least one of the light-emitting film forming step, the conductive film forming step and the insulating film forming step is carried out while holding a substrate having the electrode in a manner that an angle subtended by a surface of the substrate and the direction of gravity is within a range of from 0 to 30°.

30. (New) A method of producing a light-emitting device according to claim 27 wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

31. (New) A method of producing a light-emitting device according to claim 27, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

32. (New) A method of producing a light-emitting device according to claim 27, wherein the conductive film is an oxide conductor film.

33. (New) A method of producing a light-emitting device according to claim 27, wherein the insulating film comprises silicon nitride.

34. (New) A method of producing a light-emitting device according to claim 28 wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

35. (New) A method of producing a light-emitting device according to claim 28, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of periodic table.

36. (New) A method of producing a light-emitting device according to claim 28, wherein the conductive film is an oxide conductor film.

37. (New) A method of producing a light-emitting device according to claim 28, wherein the insulating film comprises silicon nitride.

38. (New) A method of producing a light-emitting device according to claim 29 wherein the light-emitting film comprises at least one layer selected from the group consisting of a hole injection layer, a hole-transporting layer, a hole-blocking layer, an electron injection layer, an electron-transporting layer and an electron-blocking layer.

39. (New) A method of producing a light-emitting device according to claim 29, wherein the conductive film is a metal film comprising an element belong to the Group 1 or the Group 2 of

periodic table.

40. (New) A method of producing a light-emitting device according to claim 29, wherein the conductive film is an oxide conductor film.

41. (New) A method of producing a light-emitting device according to claim 29, wherein the insulating film comprises silicon nitride.